

<b>SANYO</b>	No.1049D	<b>2SA1253/2SC3135</b>
		PNP/NPN Epitaxial Planar Silicon Transistors
<b>High-h<sub>FE</sub>, AF Amp Applications</b>		

**Features**

- High V<sub>EBO</sub>
- Wide ASO and high durability against breakdown

( ) : 2SA1253

**Absolute Maximum Ratings/T<sub>a</sub> = 25°C**

			unit
Collector to base voltage	V <sub>CB0</sub>	(-)60	V
Collector to emitter voltage	V <sub>CEO</sub>	(-)50	V
Emitter to base voltage	V <sub>EBO</sub>	(-)15	V
Collector current	I <sub>C</sub>	(-)200	mA
Collector Current(Pulse)	I <sub>CP</sub>	(-)400	mA
Collector dissipation	P <sub>C</sub>	250	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

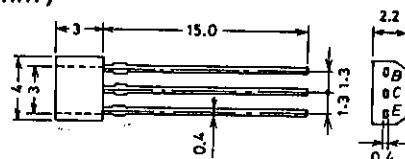
**Electrical Characteristics/T<sub>a</sub> = 25°C**

			min	typ	max	unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = (-)40V, I <sub>E</sub> = 0			(-)0.1	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = (-)10V, I <sub>C</sub> = 0			(-)0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = (-)6V, I <sub>C</sub> = (-)1mA	100*		560*	
Gain-bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = (-)6V, I <sub>C</sub> = (-)1mA		100		MHz
Common base output capacitance	c <sub>ob</sub>	V <sub>CB</sub> = (-)6V, f = 1MHz		(3.8)		pF
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = (-)50mA, I <sub>B</sub> = (-)5mA		(-0.2)	(-)0.5	V
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = (-)10μA, I <sub>E</sub> = 0	(-)60			V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = (-)1mA, R <sub>BE</sub> = ∞	(-)50			V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = (-)10μA, I <sub>C</sub> = 0	(-)15			V

\* The 2SA1253/2SC3135 are classified by 1 mA h<sub>FE</sub> as follows:

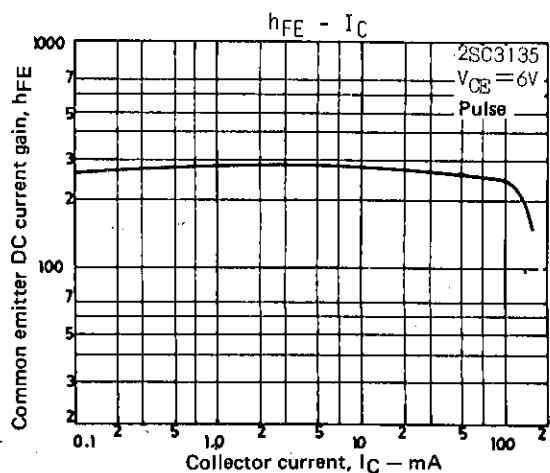
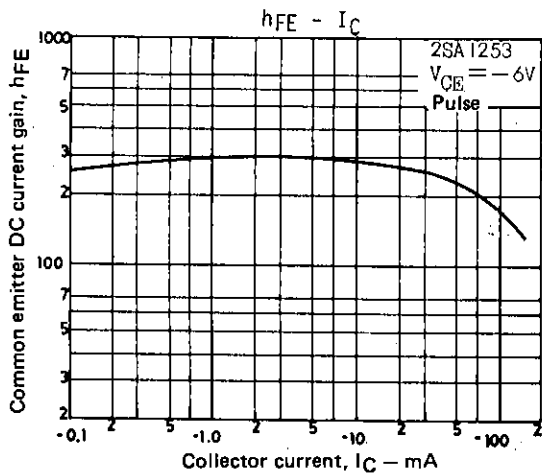
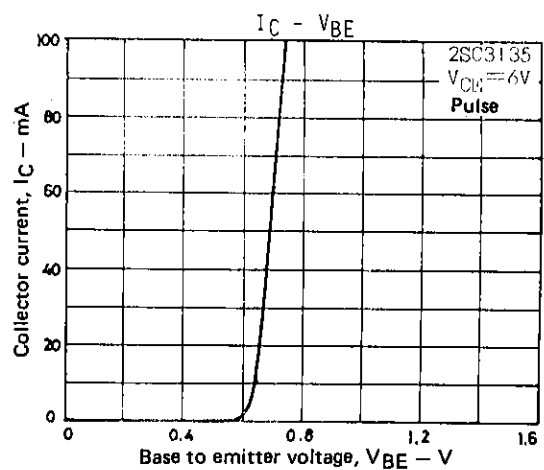
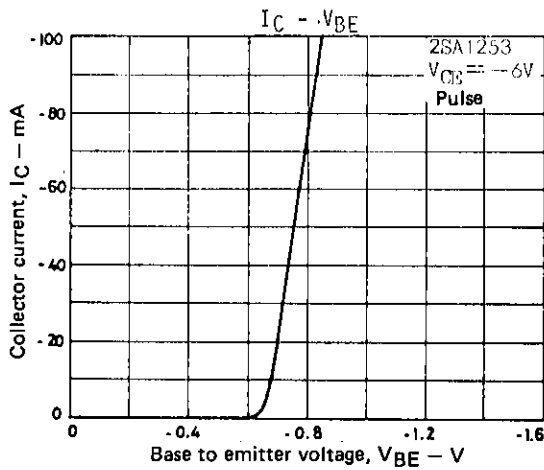
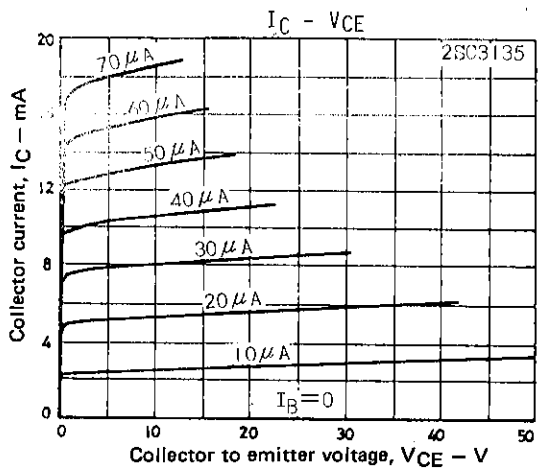
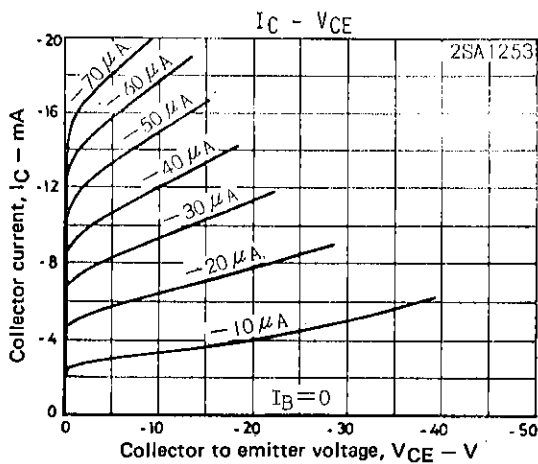
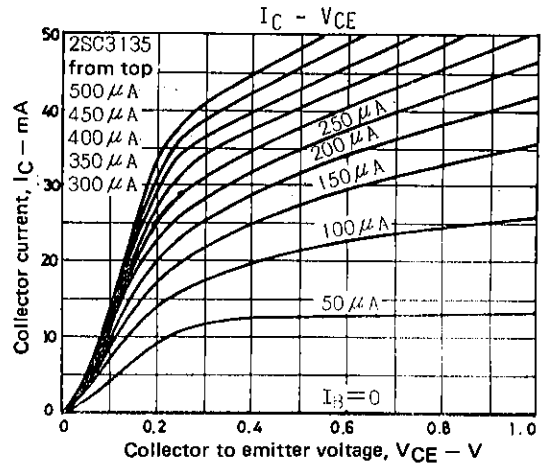
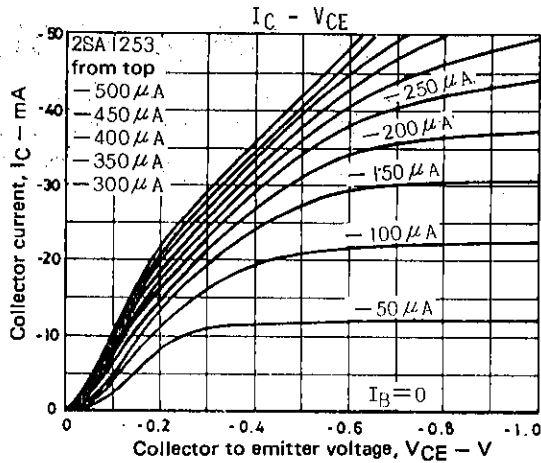
100 R	200	140 S	280	200 T	400	280 U	560
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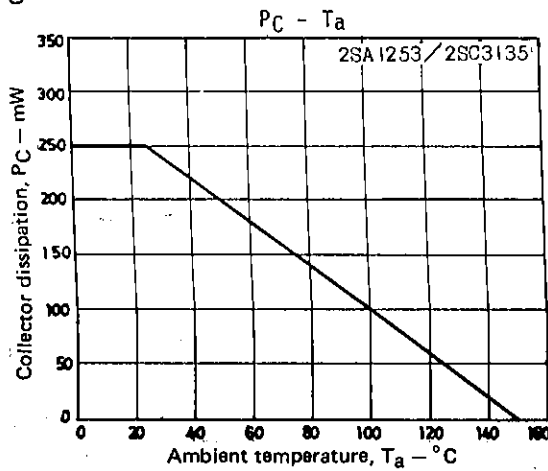
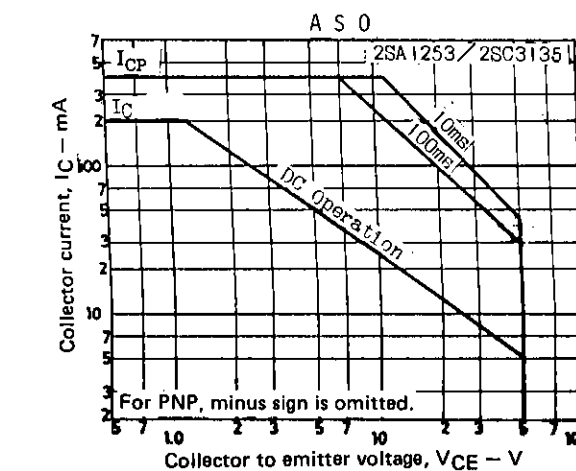
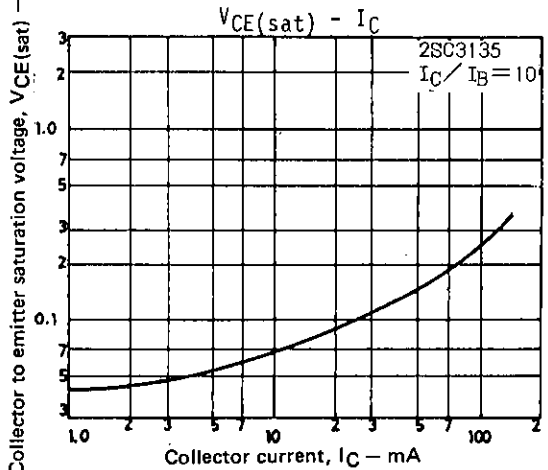
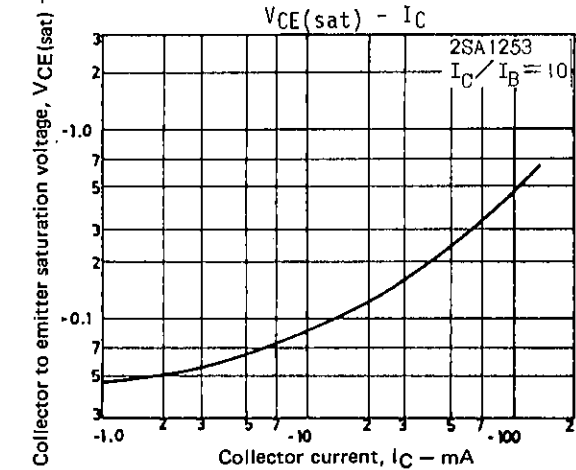
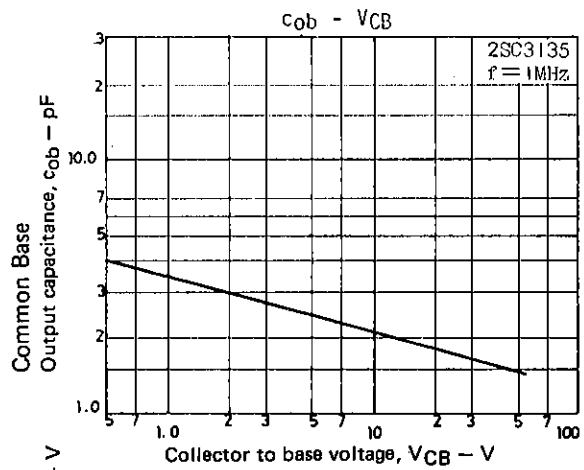
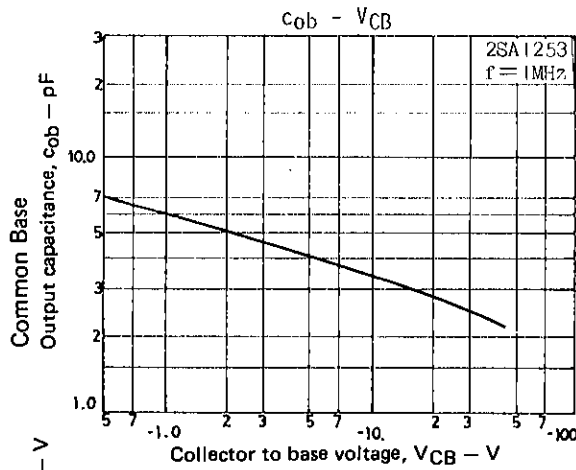
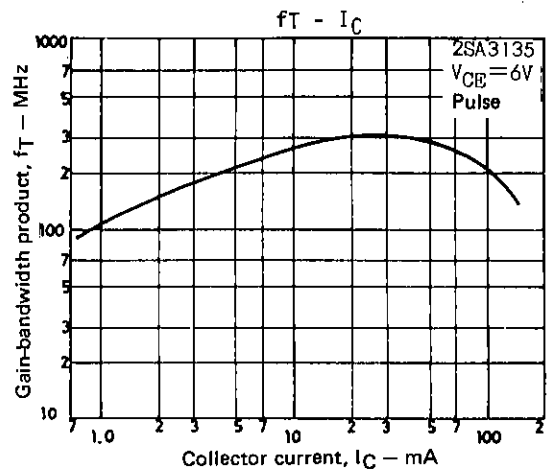
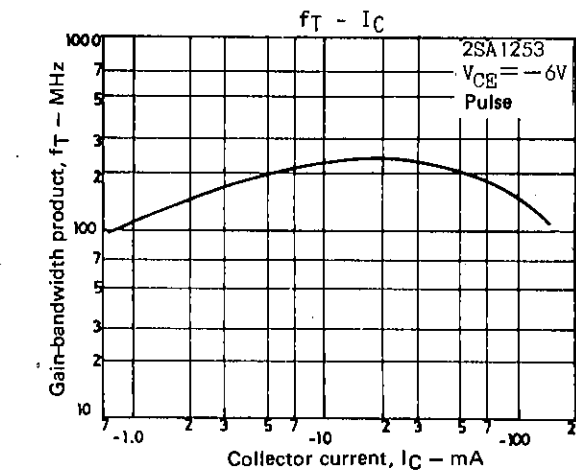
**Package Dimensions 2033**  
(unit: mm)



B: Base  
C: Collector  
E: Emitter

SANYO: SPA





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